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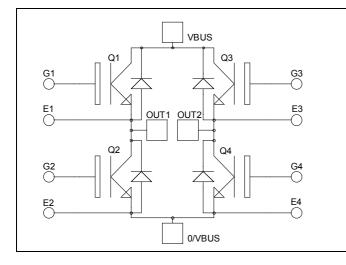
Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

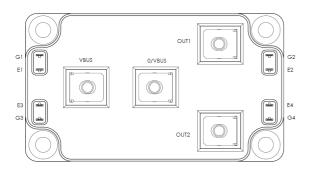




APTGT200H120G

Full - Bridge Fast Trench + Field Stop IGBT3 Power Module





$V_{CES} = 1200V$ $I_{C} = 200A$ @ Tc = 80°C

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Fast Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
 - Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
I _C	Continuous Collector Current	$T_C = 25^{\circ}C$	280	
	Continuous Conector Current	$T_C = 80^{\circ}C$	200	А
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	400	
V_{GE}	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	890	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	400A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				350	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 200A$	$T_j = 25^{\circ}C$	1.4	1.7	2.1	V
V _{CE(sat)}			$T_{j} = 125^{\circ}C$		2.0		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 3 \text{ mA}$		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				500	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			14		
Coes	Output Capacitance				0.8		nF
C _{res}	Reverse Transfer Capacitance				0.6		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)			260		
Tr	Rise Time	$V_{GE} = \pm 15V$			30		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 200A$			420		ns
$T_{\rm f}$	Fall Time	$R_G = 2.7\Omega$		70			
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 200A$ $R_G = 2.7\Omega$			290		ns
Tr	Rise Time				50		
T _{d(off)}	Turn-off Delay Time				520		
$T_{\rm f}$	Fall Time				90		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 125^{\circ}C$		20		mI
E _{off}	Turn off Energy	$I_{\rm C} = 200 \text{A}$ $R_{\rm G} = 2.7 \Omega$	$T_j = 125^{\circ}C$		20		mJ

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_i = 25^{\circ}C$ $T_i = 125^{\circ}C$			350 600	μΑ
I _F	DC Forward Current		$Tc = 80^{\circ}C$		200		А
V _F	Diode Forward Voltage	$I_{\rm F} = 200 {\rm A} \\ V_{\rm GE} = 0 {\rm V} $	$T_i = 25^{\circ}C$		1.6	2.1	V
▼ F			$T_{i} = 125^{\circ}C$		1.6		v
t _{rr}	Reverse Recovery Time	1 200 4	$T_j = 25^{\circ}C$		170		ns
۹rr			$T_{j} = 125^{\circ}C$		280		115
Q _{rr}	Reverse Recovery Charge	$I_{\rm F} = 200 \text{A}$ $V_{\rm R} = 600 \text{V}$ $di/dt = 2500 \text{A}/\mu \text{s}$	$T_j = 25^{\circ}C$		18		uС
Qrr	Reverse Recovery Charge		$T_{j} = 125^{\circ}C$		36		μC
Er	Reverse Recovery Energy		$T_j = 25^{\circ}C$		10		mI
		$T_j = 125^{\circ}C$			18		mJ

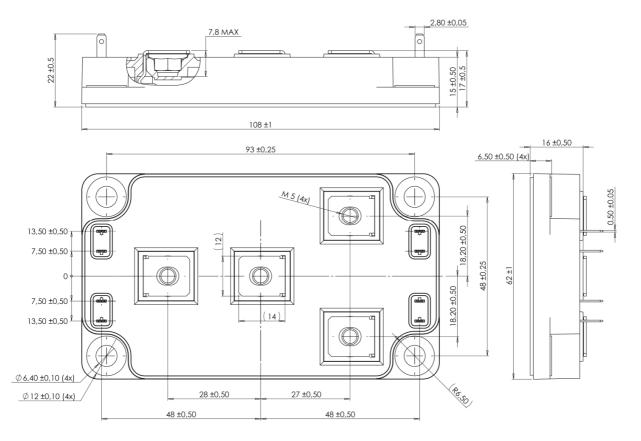
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Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance IGBT Diode				0.14	°C/W	
R _{th} JC					0.25		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Torque		For terminals	M5	2		3.5	19.111
Wt	Package Weight					300	g

SP6 Package outline (dimensions in mm)



See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

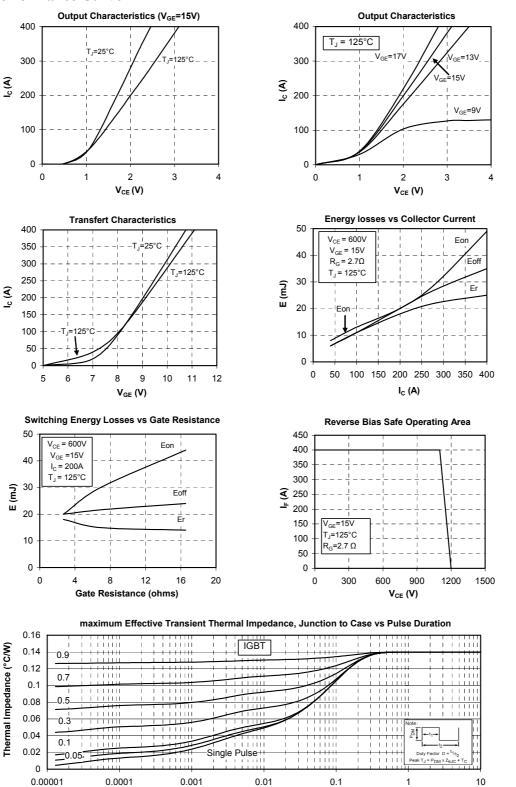
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Typical Performance Curve

I_c (A)

Thermal Impedance (°C/W)



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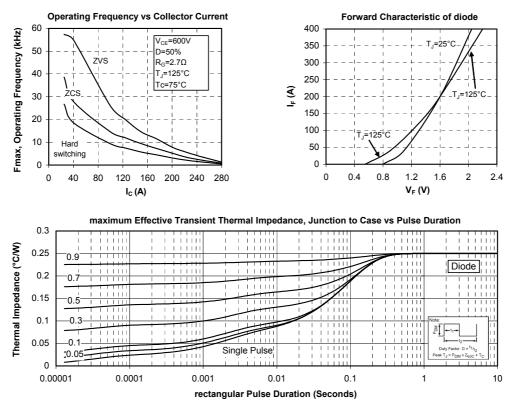
rectangular Pulse Duration (Seconds)

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APTGT200H120G

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